# P-Channel 20-V (D-S) MOSFET

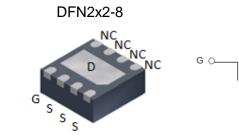
### **Key Features:**

- Low r<sub>DS(on)</sub> trench technology
- · Low thermal impedance
- 2mm x 2mm footprint DFN package
- RDS rated at 1.8V Gate-drive

### **Typical Applications:**

- Battery Powered Instruments
- Portable Computing
- Mobile Phones
- GPS Units and Media Players

PRODUCT SUMMARY			
VDS (V)	$r_{DS(on)}(m\Omega)$	Id(A)	
-20	42 @ V <sub>GS</sub> = -4.5V	-6.6	
	57 @ V <sub>GS</sub> = -2.5V	-5.7	
	86 @ V <sub>GS</sub> =-1.8V	-1	



P-Channel MOSFET

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ABSOLUTE MAXIMUM RATINGS ( $T_A = 25^{\circ}C$ UNLESS OTHERWISE NOTED)						
Parameter			Limit	Units		
Drain-Source Voltage			-20	V		
Gate-Source Voltage		V <sub>GS</sub>	±8	v		
Continuous Drain Current <sup>a</sup>	T <sub>A</sub> =25°C	1_	-6.6			
	T <sub>A</sub> =70°C	I <sub>D</sub>	-5.3	А		
Pulsed Drain Current <sup>b</sup>		I <sub>DM</sub>	-20			
Continuous Source Current (Diode Conduction) <sup>a</sup>			4	А		
Dower Discipution <sup>a</sup>	T <sub>A</sub> =25°C	P <sub>D</sub>	3	W		
Power Dissipation <sup>a</sup>	T <sub>A</sub> =70°C	١D	1.92			
Operating Junction and Storage Temperature Range			-55 to 150	°C		

RoHS

COMPLIANT

HALOGEN

THERMAL RESISTANCE RATINGS						
Parameter			Maximum	Units		
Maximum Junction-to-Ambient <sup>a</sup>	t <= 5 sec	R <sub>θJA</sub>	40	°C/W		
	Steady State		90			

Notes

- a. Surface Mounted on 1" x 1" FR4 Board.
- b. Pulse width limited by maximum junction temperature

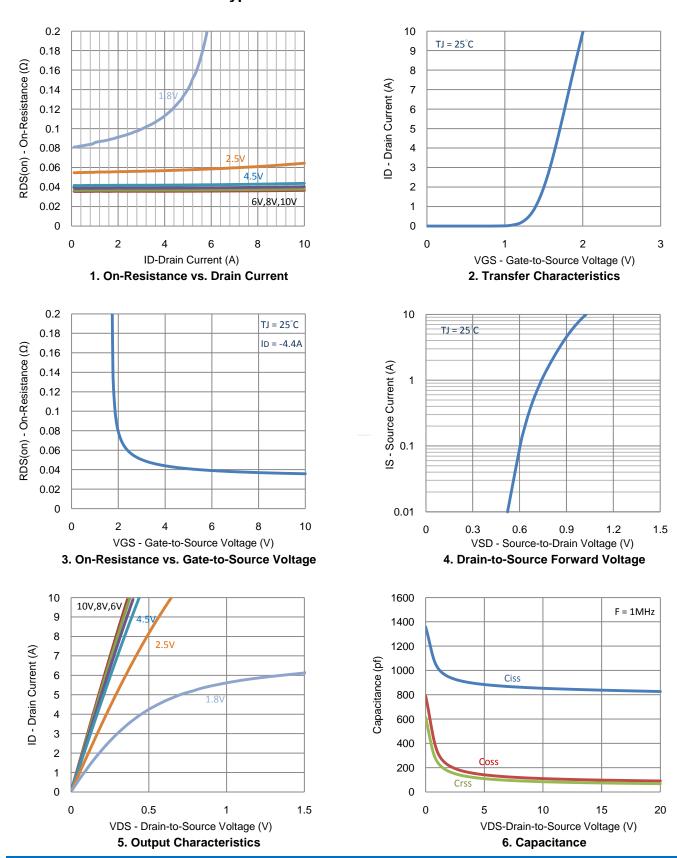
## **Electrical Characteristics**

Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit	
Static							
Gate-Source Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS} = V_{GS}, I_{D} = -250 \text{ uA}$	-0.4			V	
Gate-Body Leakage	I <sub>GSS</sub>	$V_{DS} = 0 V, V_{GS} = -8 V$			±100	nA	
Zero Gate Voltage Drain Current	1	$V_{DS} = -16 \text{ V}, V_{GS} = 0 \text{ V}$			1	uA	
	I <sub>DSS</sub>	$V_{DS} = -16 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55^{\circ}\text{C}$			25		
On-State Drain Current	I <sub>D(on)</sub>	$V_{DS} = -5 \text{ V}, \text{ V}_{GS} = -4.5 \text{ V}$	-10			А	
Drain-Source On-Resistance		$V_{GS} = -4.5 \text{ V}, \text{ I}_{D} = -4.4 \text{ A}$			42	mΩ	
	r <sub>DS(on)</sub>	$V_{GS}$ = -2.5 V, $I_{D}$ = -3.6 A			57		
		$V_{GS} = -1.8 \text{ V}, I_D = -1 \text{ A}$			86		
Forward Transconductance	<b>g</b> <sub>fs</sub>	$V_{DS} = -15 \text{ V}, \text{ I}_{D} = -4.4 \text{ A}$		20		S	
Diode Forward Voltage	$V_{SD}$	$I_{\rm S} = -2$ A, $V_{\rm GS} = 0$ V		0.83		V	
		Dynamic					
Total Gate Charge	Qg	V <sub>DS</sub> = -10 V, V <sub>GS</sub> = -4.5 V,		6.8		nC	
Gate-Source Charge	Q <sub>gs</sub>	$V_{\rm DS} = -10$ V, $V_{\rm GS} = -4.3$ V, $I_{\rm D} = -4.4$ A		1.8			
Gate-Drain Charge	$Q_{gd}$	B – 4.4 M		2.3			
Turn-On Delay Time	t <sub>d(on)</sub>			6		ns	
Rise Time	t <sub>r</sub>	$V_{DD}$ = -10 V, $R_L$ = 2.3 $\Omega$ , $I_D$ = -4.4 A,		6			
Turn-Off Delay Time	t <sub>d(off)</sub>	$V_{GEN}$ = -4.5 V, $R_{GEN}$ = 6 $\Omega$		23			
Fall Time	t <sub>f</sub>			15			
Input Capacitance	C <sub>iss</sub>			837			
Output Capacitance	C <sub>oss</sub>	$V_{DS} = -15 V, V_{GS} = 0 V, f = 1 MHz$		98		pF	
Reverse Transfer Capacitance	C <sub>rss</sub>			75			
Gate Resistance	R <sub>g</sub>	f = 1 MHz		3.7		Ω	

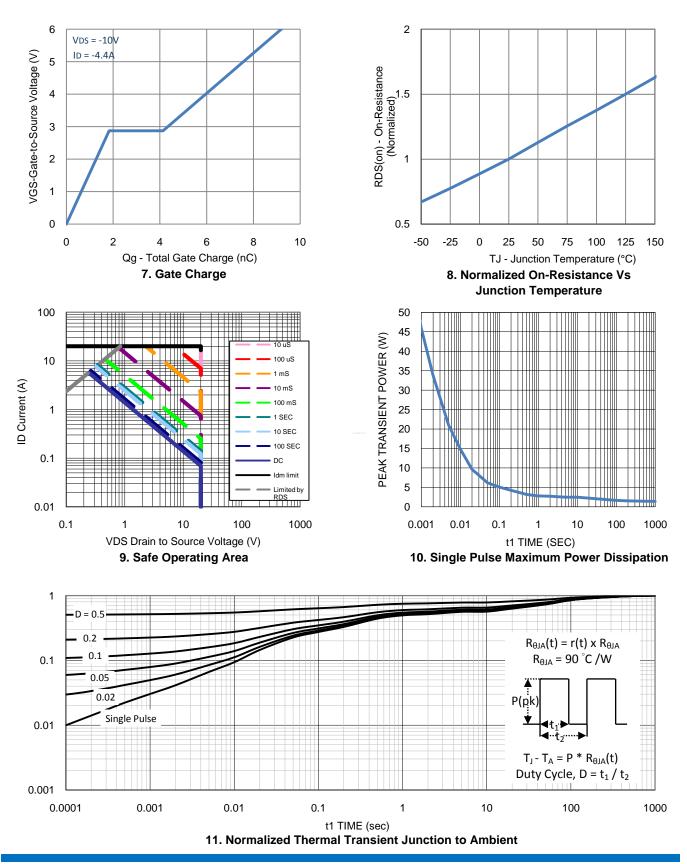
#### Notes

- a. Pulse test: PW <= 300us duty cycle <= 2%.
- b. Guaranteed by design, not subject to production testing.

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# **Typical Electrical Characteristics**



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# **Package Information**

